

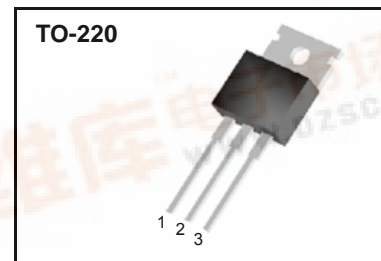
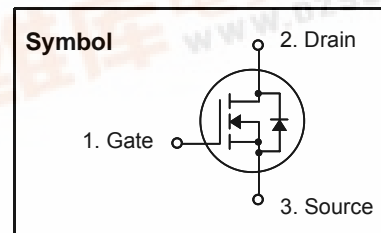
**N-Channel MOSFET**

**Features**

- Low  $R_{DS(on)}$  ( $0.023 \Omega$ )@ $V_{GS}=10V$
- Low Gate Charge (Typical 39nC)
- Low  $C_{rss}$  (Typical 110pF)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Maximum Junction Temperature Range (175°C)

**General Description**

This Power MOSFET is produced using SemiWell's advanced planar stripe, DMOS technology. This latest technology has been especially designed to minimize on-state resistance, have a low gate charge with superior switching performance, and rugged avalanche characteristics. This Power MOSFET is well suited for synchronous DC-DC Converters and Power Management in portable and battery operated products.



**Absolute Maximum Ratings**

Symbol	Parameter	Value	Units
$V_{DSS}$	Drain to Source Voltage	60	V
$I_D$	Continuous Drain Current(@ $T_C = 25^\circ C$ )	50	A
	Continuous Drain Current(@ $T_C = 100^\circ C$ )	35.2	A
$I_{DM}$	Drain Current Pulsed (Note 1)	200	A
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	470	mJ
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	13	mJ
$I_{AR}$	Avalanche Current (Note 1)	50	A
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7	V/ns
$P_D$	Total Power Dissipation(@ $T_C = 25^\circ C$ )	130	W
	Derating Factor above $25^\circ C$	0.87	W/ $^\circ C$
$T_{STG}, T_J$	Operating Junction Temperature & Storage Temperature	- 55 ~ 175	$^\circ C$
$T_L$	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.	300	$^\circ C$

**Thermal Characteristics**

Symbol	Parameter	Value			Units
		Min.	Typ.	Max.	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	-	-	1.15	$^\circ C/W$
$R_{\theta CS}$	Thermal Resistance, Case to Sink	-	0.5	-	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	-	-	62.5	$^\circ C/W$



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## Electrical Characteristics ( $T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted )

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	60	-	-	V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature coefficient	$I_D = 250\mu A$ , referenced to $25\text{ }^\circ\text{C}$	-	0.06	-	V/ $^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS} = 60V, V_{GS} = 0V$	-	-	1	$\mu A$
		$V_{DS} = 48V, T_C = 150\text{ }^\circ\text{C}$	-	-	10	$\mu A$
$I_{GSS}$	Gate-Source Leakage, Forward	$V_{GS} = 20V, V_{DS} = 0V$	-	-	100	nA
	Gate-source Leakage, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	-	-	-100	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	-	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-state Resistance	$V_{GS} = 10V, I_D = 25A$	-	0.018	0.023	$\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{GS} = 0V, V_{DS} = 25V, f = 1\text{MHz}$	-	880	1140	pF
$C_{oss}$	Output Capacitance		-	430	560	
$C_{rss}$	Reverse Transfer Capacitance		-	110	140	
<b>Dynamic Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 30V, I_D = 25A, R_G = 50\Omega$ * see fig. 13. (Note 4, 5)	-	60	130	ns
$t_r$	Rise Time		-	185	380	
$t_{d(off)}$	Turn-off Delay Time		-	75	160	
$t_f$	Fall Time		-	60	130	
$Q_g$	Total Gate Charge		$V_{DS} = 48V, V_{GS} = 10V, I_D = 50A$ * see fig. 12. (Note 4, 5)	-	39	
$Q_{gs}$	Gate-Source Charge	-		9.5	-	
$Q_{gd}$	Gate-Drain Charge(Miller Charge)	-		13	-	

## Source-Drain Diode Ratings and Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit.
$I_S$	Continuous Source Current	Integral Reverse p-n Junction Diode in the MOSFET	-	-	50	A
$I_{SM}$	Pulsed Source Current		-	-	200	
$V_{SD}$	Diode Forward Voltage	$I_S = 50A, V_{GS} = 0V$	-	-	1.5	V
$t_{rr}$	Reverse Recovery Time	$I_S = 50A, V_{GS} = 0V, di_F/dt = 100A/\mu s$	-	54	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	81	-	nC

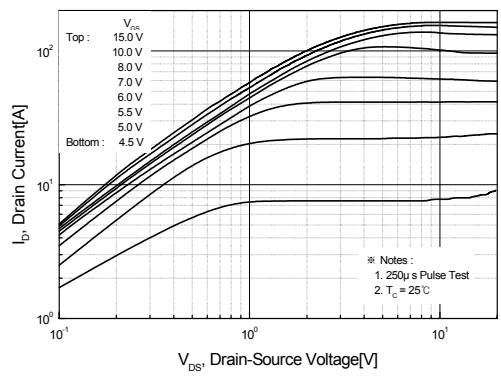
### \* NOTES

1. Repeatability rating : pulse width limited by junction temperature,  $\delta < 1\%$
2.  $L = 220\mu H, I_{AS} = 50A, V_{DD} = 25V, R_G = 0\Omega$ , Starting  $T_J = 25\text{ }^\circ\text{C}$
3.  $I_{SD} \leq 50A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25\text{ }^\circ\text{C}$
4. Pulse Test : Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$
5. Essentially independent of operating temperature.

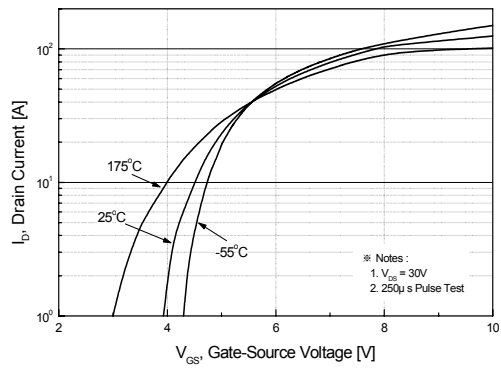


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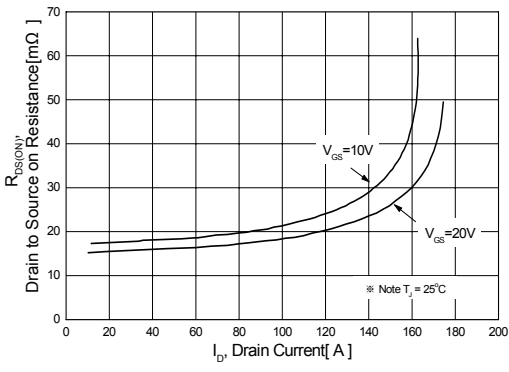
**Fig 1. On-State Characteristics**



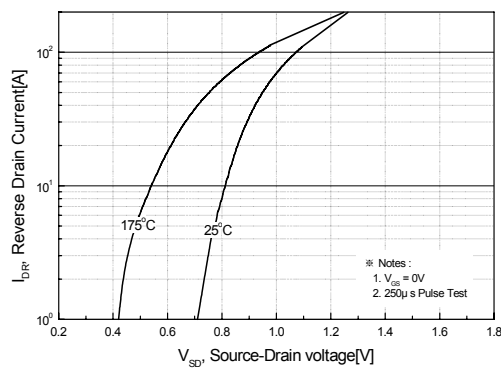
**Fig 2. Transfer Characteristics**



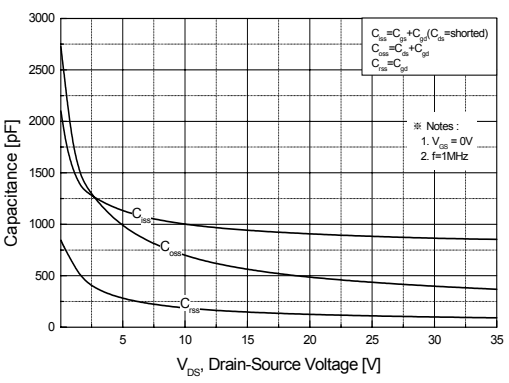
**Fig 3. On Resistance Variation vs. Drain Current and Gate Voltage**



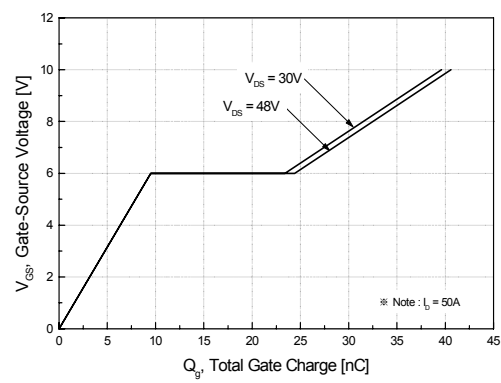
**Fig 4. On State Current vs. Allowable Case Temperature**



**Fig 5. Capacitance Characteristics**

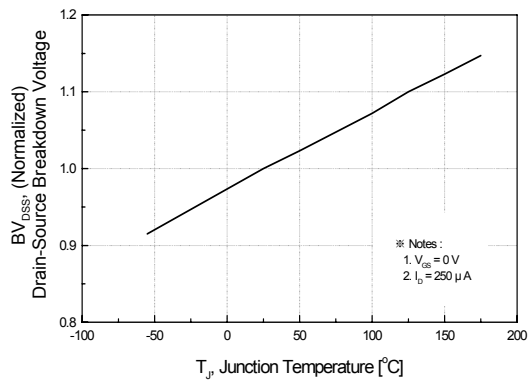


**Fig 6. Gate Charge Characteristics**

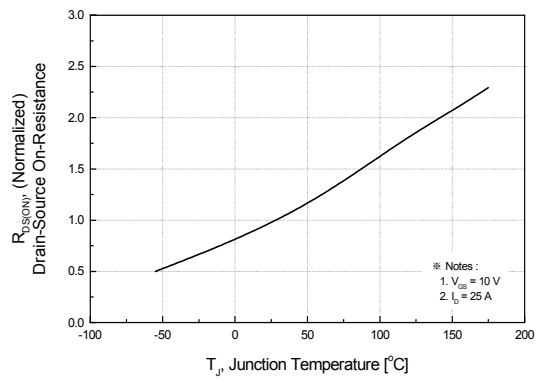


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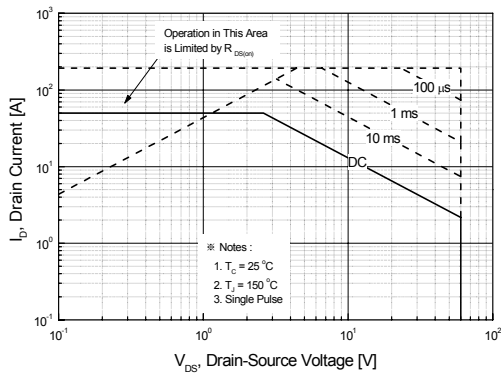
**Fig 7. Breakdown Voltage Variation vs. Junction Temperature**



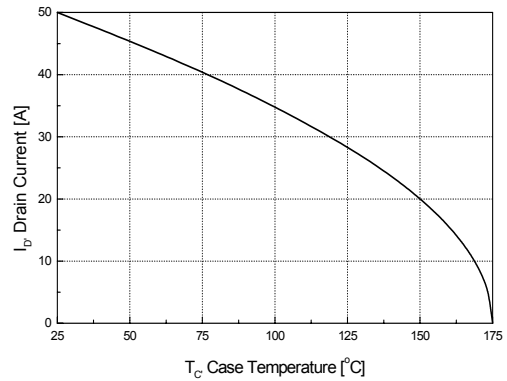
**Fig 8. On-Resistance Variation vs. Junction Temperature**



**Fig 9. Maximum Safe Operating Area**



**Fig 10. Maximum Drain Current vs. Case Temperature**



**Fig 11. Transient Thermal Response Curve**

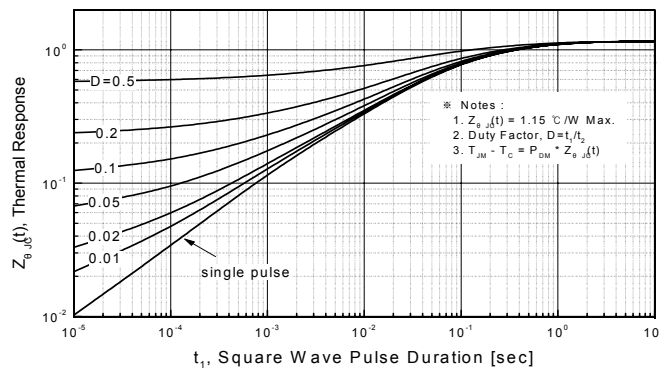


Fig. 12. Gate Charge Test Circuit & Waveforms

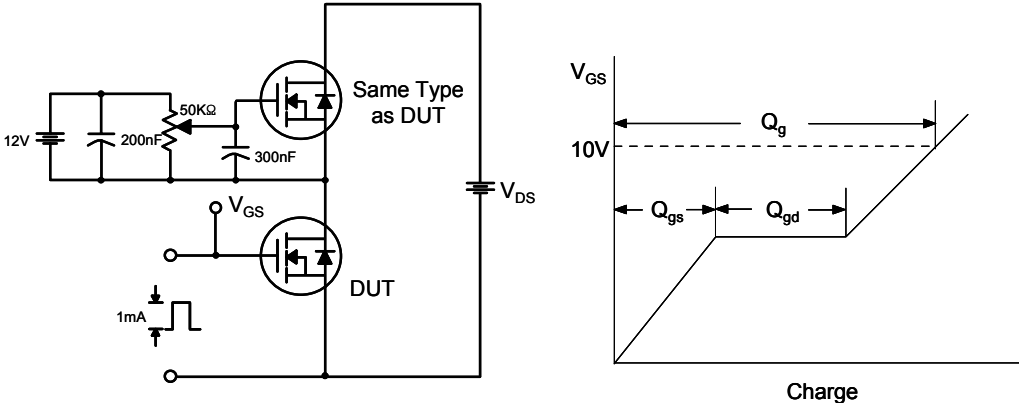


Fig 13. Switching Time Test Circuit & Waveforms

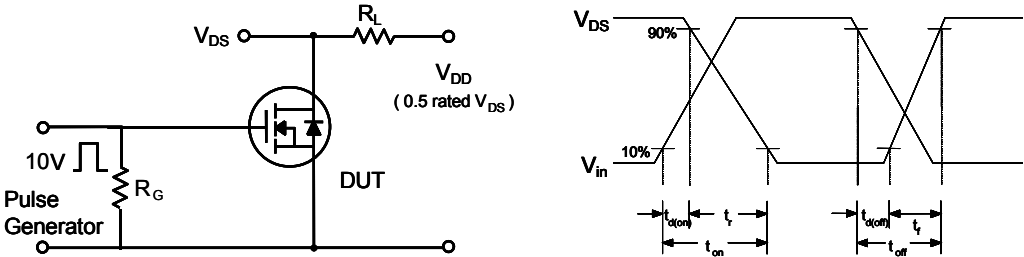
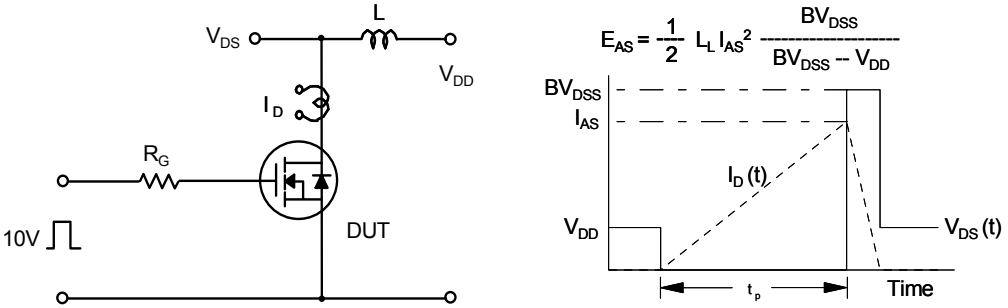
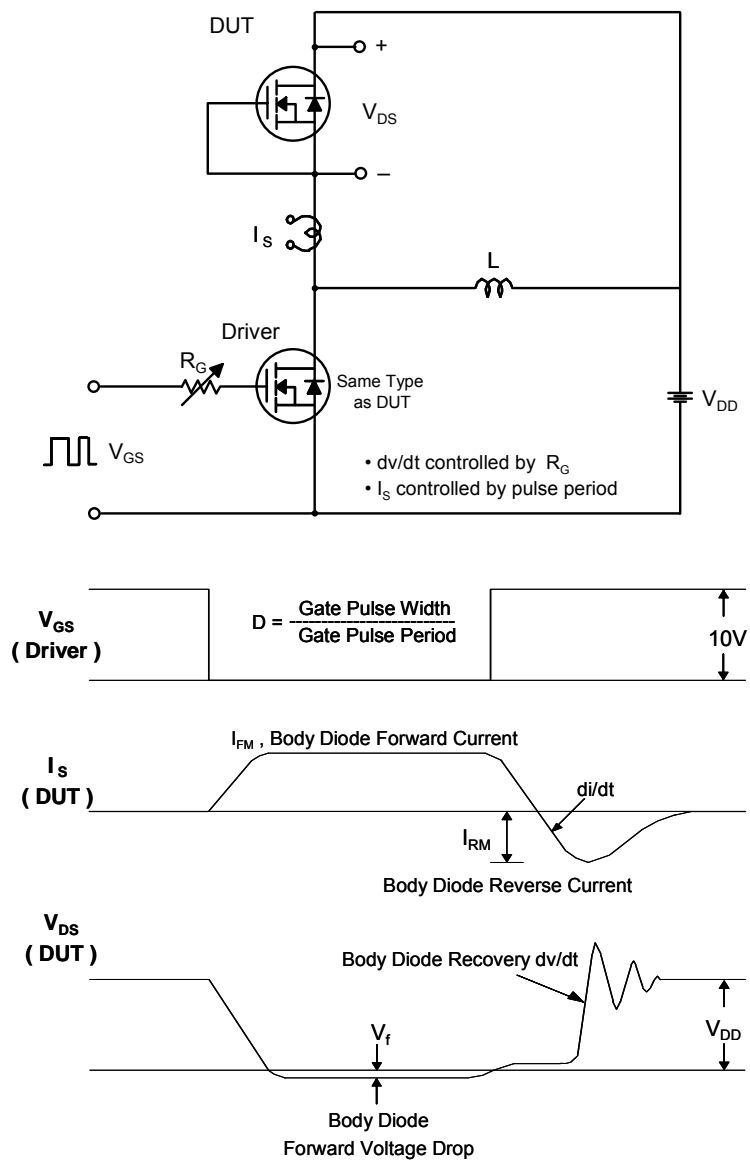


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms



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Fig. 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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## TO-220 Package Dimension

Dim.	mm			Inch		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.7		10.1	0.382		0.398
B	6.3		6.7	0.248		0.264
C	9.0		9.47	0.354		0.373
D	12.8		13.3	0.504		0.524
E	1.2		1.4	0.047		0.055
F		1.7			0.067	
G		2.5			0.098	
H	3.0		3.4	0.118		0.134
I	1.25		1.4	0.049		0.055
J	2.4		2.7	0.094		0.106
K	5.0		5.15	0.197		0.203
L	2.2		2.6	0.087		0.102
M	1.25		1.55	0.049		0.061
N	0.45		0.6	0.018		0.024
O	0.6		1.0	0.024		0.039
∅		3.6			0.142	

